

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S22	5187	('soi' silicon adj on adj insulat\$3) with (dop\$4 implant\$5 diffus\$4)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/03/03 06:22
S23	4133	S22 and ((impurit\$3 ion type) with (dop\$4 implant\$5 diffus\$4))	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/03/03 06:24
S24	1981	S23 and ((mask\$3 photoresist resist) with (dop\$4 implant\$5 diffus\$4))	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/03/03 06:25
S25	1545	S24 and ((source drain s/d) with (dop\$4 implant\$5 diffus\$4))	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/03/03 06:28
S26	1006	S25 and ((mask\$3 photoresist resist) with gate)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/03/03 06:25
S27	363	S26 and (active adj region)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/03/03 06:28
S28	270	S27 and (first with (dop\$4 implant\$5 diffus\$4))	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/03/03 06:29
S29	234	S28 and (second with (dop\$4 implant\$5 diffus\$4))	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/03/03 06:29
S30	89	S29 and (third with (dop\$4 implant\$5 diffus\$4))	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/03/03 06:31
S31	169	S29 and (boron with (dop\$4 implant\$5 diffus\$4))	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/03/03 06:30

S32	22	S29 and (indium with (dop\$4 implant\$5 diffus\$4))	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/03/03 06:30
S33	36	S29 and (antimony with (dop\$4 implant\$5 diffus\$4))	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/03/03 06:30